

## **Silicon nitride deposition for organic electronics by VHF (162MHz)- PECVD**

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Deposition of permeation barrier film for organic-based electronics is one of the most important issues in organic electronic device fabrication process because the permeation of moisture and oxygen into organic materials causes significant degradation of the device performance and stability. In this study, as an effective thin film barrier material for organic electronics, we investigated low-temperature ( $\sim 80$  °C) silicon nitride deposited by very high frequency (VHF, 162MHz) PECVD using multi-tile push-pull electrodes with a gas mixture of  $\text{NH}_3/\text{SiH}_4$ . The composition of the silicon nitride film deposited by VHF PECVD was similar to the ideal stoichiometry of silicon nitride ( $\text{Si} : \text{N} = 1 : 1.33$ ) and the deposited film exhibited high optical transparency over 90% in the visible region. The deposited silicon nitride also exhibited a high step coverage of 1:1.29. When water vapor transmission rate (WVTR) was measured with single (400 nm thick)  $\text{SiN}_x$  layer deposited on PET, excellent WVTR of  $4.39 \times 10^{-4}$  g/m<sup>2</sup>-day could be obtained. I-V characteristics of organic light emitting diode (OLED) devices were measured before and after the film deposition on the devices, and no noticeable changes of I-V characteristics after the deposition of silicon nitride film on the OLED devices were observed indicating no noticeable electrical damage by the deposition of silicon nitride using VHF PECVD which is ascribed by low electron temperature characteristics of the plasma and the lack of current flow to the substrate for the VHF-PECVD method utilizing multi-tile push-pull-type electrodes.

Keywords : encapsulation, silicon nitride, organic light emitting diode (OLED), very high frequency (VHF), water vapor transmission rate (WVTR), step coverage